

## PATENT ASSIGNMENT COVER SHEET

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 Stylesheet Version v1.2

EPAS ID: PAT3861059

<b>SUBMISSION TYPE:</b>	NEW ASSIGNMENT
<b>NATURE OF CONVEYANCE:</b>	ASSIGNMENT
<b>CONVEYING PARTY DATA</b>	
<b>Name</b>	<b>Execution Date</b>
HUSSAIN H. LADHANI	07/02/2010
GERARD J. BOUISSE	06/22/2010
JEFFREY K. JONES	06/24/2010
<b>RECEIVING PARTY DATA</b>	
<b>Name:</b>	Freescall Semiconductor, Inc.
<b>Street Address:</b>	6501 William Cannon Drive West
<b>Internal Address:</b>	Law Department
<b>City:</b>	Austin
<b>State/Country:</b>	TEXAS
<b>Postal Code:</b>	78735
<b>PROPERTY NUMBERS Total: 1</b>	
<b>Property Type</b>	<b>Number</b>
Application Number:	14942419
<b>CORRESPONDENCE DATA</b>	
<b>Fax Number:</b>	(512)895-6630
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>	
<b>Phone:</b>	512-895-6979
<b>Email:</b>	sheena.hicks@nxp.com
<b>Correspondent Name:</b>	FREESCALE SEMICONDUCTOR, INC.
<b>Address Line 1:</b>	6501 WILLIAM CANNON DRIVE WEST
<b>Address Line 2:</b>	TX30/OE62
<b>Address Line 4:</b>	AUSTIN, TEXAS 78735
<b>ATTORNEY DOCKET NUMBER:</b>	RA48567ZC-US05
<b>NAME OF SUBMITTER:</b>	SHEENA HICKS
<b>SIGNATURE:</b>	/Sheena Hicks/
<b>DATE SIGNED:</b>	05/05/2016
<b>Total Attachments: 8</b>	
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## ASSIGNMENT AND AGREEMENT

For good and valuable consideration, the receipt of which is hereby acknowledged, we, **HUSSAIN H. LADHANI, TEMPE, ARIZONA; GERARD J. BOUISSE, TOULOUSE, FRANCE; and, JEFFREY K. JONES, CHANDLER, ARIZONA,** have sold, assigned and transferred, and do hereby sell, assign and transfer, unto FREESCALE SEMICONDUCTOR, INC., a corporation of the State of Delaware, having its principal office in Austin, State of Texas, United States of America, and its successors, assigns, and legal representatives, the entire right, title and interest for the United States of America in and to certain inventions relating to improvements in **RF POWER TRANSISTOR CIRCUIT** (Application No. **12/746793**; Docket No. **RA48567ZC**), described, illustrated and claimed in an application for Letters Patent of the United States of America executed by us on the dates indicated by our signatures below, together with the entire right, title and interest in and to the application, and in and to Letters Patent which may be issued upon the application, and upon any division, extension, continuation or reissue thereof.

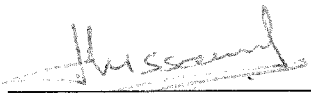
We hereby also sell, assign and transfer unto FREESCALE SEMICONDUCTOR, INC., the entire right, title and interest in and to the invention and in and to applications for Letters Patent therefor in all countries foreign to the United States of America, including all rights under any and all international conventions and treaties in respect of the invention and the applications for Letters Patent in foreign countries, and we further authorize FREESCALE SEMICONDUCTOR, INC. to apply for Letters Patent in foreign countries directly in its own name, and to claim priority of the filing date of the application for Letters Patent of the United States of America under the provisions of any and all international conventions and treaties.

We hereby authorize and request the Commissioner of Patents of the United States of America to issue Letters Patent upon the aforesaid application, division, extension, continuation or reissue, to FREESCALE SEMICONDUCTOR, INC., for the sole use and benefit of FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives, to the full end of the term for which Letters Patent may be granted, the same as they would have been held and enjoyed by me had this assignment not been made, and we hereby authorize and request the equivalent authorities in foreign countries to issue the patents of their respective countries to FREESCALE SEMICONDUCTOR, INC.

We agree that, when requested, we will, without charge to FREESCALE SEMICONDUCTOR, INC., but at its expense, sign all papers, take all rightful oaths, and do all acts which may be necessary, desirable or convenient for securing and maintaining patents for

the inventions in any and all countries and for vesting title thereto in FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives or nominees.

We covenant with FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives, that the interest and property hereby conveyed is free from all prior assignment, grant, mortgage, license or other encumbrance.

  
\_\_\_\_\_  
HUSSAIN H. LADHANI

DATE: 07/02/2010

**First Witness**

  
\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: 07/02/2010  
(Month-Day-Year)

RICARDO A. USCOA  
\_\_\_\_\_  
PRINTED NAME OF WITNESS

**Second Witness**

  
\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: 07/06/2010  
(Month-Day-Year)

Nick Yang  
\_\_\_\_\_  
PRINTED NAME OF WITNESS

\_\_\_\_\_  
GERARD J. BOUISSE

DATE: \_\_\_\_\_

**First Witness**

\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: \_\_\_\_\_  
(Month-Day-Year)

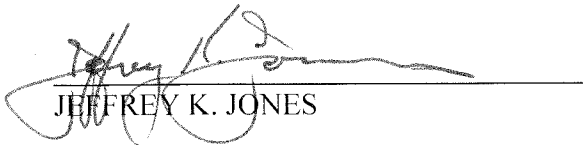
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**Second Witness**

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SIGNATURE OF WITNESS

DATE: \_\_\_\_\_  
(Month-Day-Year)

\_\_\_\_\_  
PRINTED NAME OF WITNESS

  
JEFFREY K. JONES

DATE: June 24th, 2010

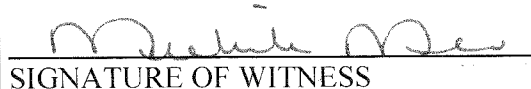
First Witness

  
SIGNATURE OF WITNESS

DATE: June 24th 2010  
(Month-Day-Year)

BASIM NOORI  
PRINTED NAME OF WITNESS

Second Witness

  
SIGNATURE OF WITNESS

DATE: June 24th 2010  
(Month-Day-Year)

Michele Miera  
PRINTED NAME OF WITNESS

PATENT

ASSIGNMENT AND AGREEMENT

For good and valuable consideration, the receipt of which is hereby acknowledged, we, **HUSSAIN H. LADHANI, TEMPE, ARIZONA; GERARD J. BOUISSE, TOULOUSE, FRANCE; and, JEFFREY K. JONES, CHANDLER, ARIZONA**, have sold, assigned and transferred, and do hereby sell, assign and transfer, unto **FREESCALE SEMICONDUCTOR, INC.**, a corporation of the State of Delaware, having its principal office in Austin, State of Texas, United States of America, and its successors, assigns, and legal representatives, the entire right, title and interest for the United States of America in and to certain inventions relating to improvements in **RF POWER TRANSISTOR CIRCUIT** (Application No. **12/746793**; Docket No. **RA48567ZC**), described, illustrated and claimed in an application for Letters Patent of the United States of America executed by us on the dates indicated by our signatures below, together with the entire right, title and interest in and to the application, and in and to Letters Patent which may be issued upon the application, and upon any division, extension, continuation or reissue thereof.

We hereby also sell, assign and transfer unto **FREESCALE SEMICONDUCTOR, INC.**, the entire right, title and interest in and to the invention and in and to applications for Letters Patent therefor in all countries foreign to the United States of America, including all rights under any and all international conventions and treaties in respect of the invention and the applications for Letters Patent in foreign countries, and we further authorize **FREESCALE SEMICONDUCTOR, INC.** to apply for Letters Patent in foreign countries directly in its own name, and to claim priority of the filing date of the application for Letters Patent of the United States of America under the provisions of any and all international conventions and treaties.

We hereby authorize and request the Commissioner of Patents of the United States of America to issue Letters Patent upon the aforesaid application, division, extension, continuation or reissue, to **FREESCALE SEMICONDUCTOR, INC.**, for the sole use and benefit of **FREESCALE SEMICONDUCTOR, INC.**, its successors, assigns and legal representatives, to the full end of the term for which Letters Patent may be granted, the same as they would have been held and enjoyed by me had this assignment not been made, and we hereby authorize and request the equivalent authorities in foreign countries to issue the patents of their respective countries to **FREESCALE SEMICONDUCTOR, INC.**

We agree that, when requested, we will, without charge to **FREESCALE SEMICONDUCTOR, INC.**, but at its expense, sign all papers, take all rightful oaths, and do all acts which may be necessary, desirable or convenient for securing and maintaining patents for

the inventions in any and all countries and for vesting title thereto in FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives or nominees.

We covenant with FREESCALE SEMICONDUCTOR, INC., its successors, assigns and legal representatives, that the interest and property hereby conveyed is free from all prior assignment, grant, mortgage, license or other encumbrance.

\_\_\_\_\_  
HUSSAIN H. LADHANI                      DATE: \_\_\_\_\_

**First Witness**

\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: \_\_\_\_\_  
(Month-Day-Year)

\_\_\_\_\_  
PRINTED NAME OF WITNESS


**Second Witness**

\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: \_\_\_\_\_  
(Month-Day-Year)

\_\_\_\_\_  
PRINTED NAME OF WITNESS



  
GERARD J. BOUISSE

DATE: June 22nd 2010


**First Witness**

  
SIGNATURE OF WITNESS

DATE: June 22nd 2010  
(Month-Day-Year)

Cédric Cassan  
PRINTED NAME OF WITNESS

**Second Witness**

  
SIGNATURE OF WITNESS

DATE: 06/22/10  
(Month-Day-Year)

LOIRAT JEAN-CLAUDE  
PRINTED NAME OF WITNESS

\_\_\_\_\_  
JEFFREY K. JONES

DATE: \_\_\_\_\_

**First Witness**

\_\_\_\_\_  
SIGNATURE OF WITNESS

DATE: \_\_\_\_\_  
(Month-Day-Year)

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PRINTED NAME OF WITNESS

**Second Witness**

\_\_\_\_\_  
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DATE: \_\_\_\_\_  
(Month-Day-Year)

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